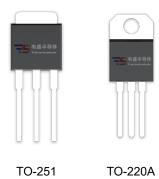


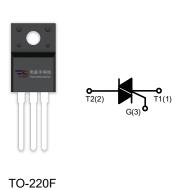
## **DESCRIPTION:**

The BTB06-600C SCR series with the parallel resistor between Gate and Cathode are especially recommended for use on straight hair, igniter, anion generator, etc.





Symbol	Symbol Value	
I <sub>T(RMS)</sub>	6	А
V <sub>DRM</sub> /V <sub>RRM</sub>	600/800	V



### **ABSOLUTE MAXIMUM RATINGS**

Parameter			Symbol	Value	Unit
Storage junction temperature range			T <sub>stg</sub>	-40 - 150	$^{\circ}$ C
Operating junction temperature range			Tj	-40 - 125	$^{\circ}$ C
Repetitive peak off-state voltage (T <sub>j</sub> =25℃)			V <sub>DRM</sub>	600/800	V
Repetitive peak reverse voltage (T <sub>j</sub> =25℃)		V <sub>RRM</sub>	600/800	V	
RMS on-state current	TO-220A(Ins)/ TO-220F(Ins)/ TO-251 (Tc=100°C) TO-220A(Non-Ins) (Tc=105°C)		I <sub>T(RMS)</sub>	6	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)			I <sub>TSM</sub>	60	Α
I <sup>2</sup> t value for fusing (tp=10ms)			l <sup>2</sup> t	18	A <sup>2</sup> s
Critical rate of rise of on-state		dl/dt	50	A/µs	
current (I <sub>G</sub> =2×I <sub>GT</sub> )		IV	ui/ut	10	7/µ3



Peak gate current	I <sub>GM</sub>	2	Α
Average gate power dissipation	P <sub>G(AV)</sub>	1	W
Peak gate power	P <sub>GM</sub>	5	W

# **ELECTRICAL CHARACTERISTICS** (T<sub>j</sub>=25°C unless otherwise specified)

Symbol	Test Condition	Quadrant		Va	lue	Unit
				С	В	
I <sub>GT</sub>	V <sub>D</sub> =12V R <sub>L</sub> =30Ω	I - II -III	MAX	25	50	mA
		IV		50	70	
V <sub>GT</sub>		ALL	MAX	1.5		V
V <sub>GD</sub>	$V_D = V_{DRM} T_j = 125$ °C $R_L = 3.3$ KΩ	ALL	MIN	0.2		V
l <sub>L</sub> I <sub>G</sub>	I <sub>G</sub> =1.2I <sub>GT</sub>	I -III-IV	MAY	50	70	mΛ
		II	MAX	60	80	mA
l <sub>Η</sub>	I <sub>TM</sub> =0.2A		MAX	40	60	mA
dV/dt	V <sub>D</sub> =2/3V <sub>DRM</sub> Gate Open T <sub>j</sub> =125℃		MIN	200	500	V/µs

## **STATIC CHARACTERISTICS**

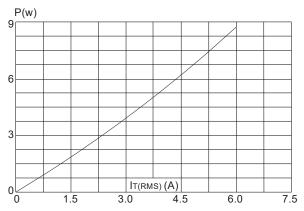
Symbol	Parameter		Value(MAX)	Unit
V <sub>TM</sub>	I <sub>тм</sub> =8.5A tp=380µs	T <sub>j</sub> =25℃	1.5	V
IDRM	V <sub>D</sub> =V <sub>DRM</sub> V <sub>R</sub> =V <sub>RRM</sub>	Tj=25℃	5	μA
I <sub>RRM</sub>		Tj=125℃	1	mA

## **THERMAL RESISTANCES**

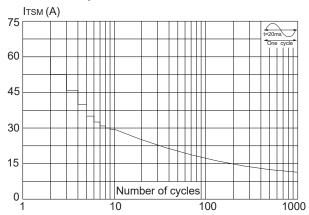
Symbol	Parameter		Value	Unit
R <sub>th(j-c)</sub> junction to case(AC)		TO-220A(Ins) TO-220F(Ins)	2.9	
	TO-220A(Non-Ins) 2.3		°C/W	
		TO-251	2.7	



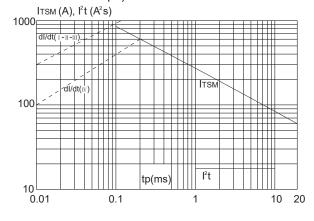
**FIG.1:** Maximum power dissipation versus RMS on-state current



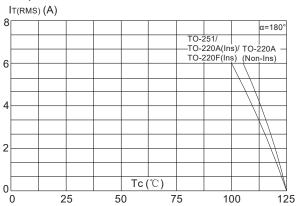
**FIG.3:** Surge peak on-state current versus number of cycles



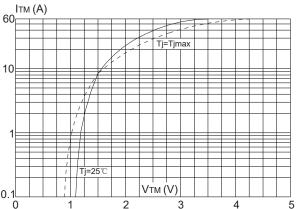
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<20ms, and corresponging value of l<sup>2</sup>t ( I - II - III:dl/dt < 50A/μs; IV:dl/dt < 10A/μs)



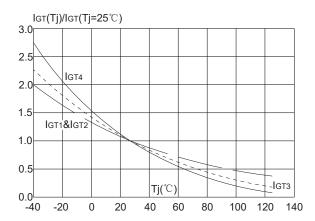
**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics (maximum values)

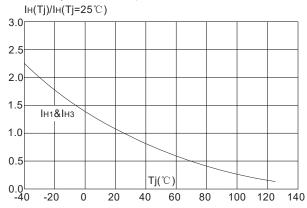


**FIG.6:** Relative variations of gate trigger current versus junction temperature





**FIG.7:** Relative variations of holding current versus junction temperature



**FIG.8:** Relative variations of latching current versus junction temperature

